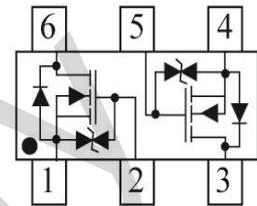
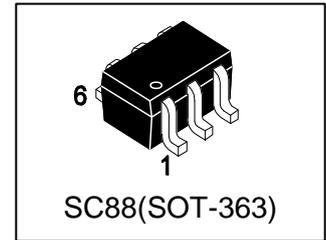


# LSI1012DW1T1G

## S-LSI1012DW1T1G

N-Channel Enhancement Mode MOSFET



### 1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.
- Surface-mounted package.
- Extremely low threshold voltage
- Advanced trench cell design
- Gate to Source ESD protected:  
HBM>2KV

### 2. APPLICATION

- Portable appliances

### 3. DEVICE MARKING AND ORDERING INFORMATION

| Device        | Marking | Shipping       |
|---------------|---------|----------------|
| LSI1012DW1T1G | 9D      | 3000/Tape&Reel |

### 4. MAXIMUM RATINGS(Ta = 25°C)

| Parameter  | Symbol | Limits   | Unit |
|--|--------|----------|------|
| Drain-Source Voltage                             | VDSS   | 20       | V    |
| Gate-Source Voltage                              | VGSS   | ±10      | V    |
| Drain Current<br>(TA = 25 °C, VGS = 10 V)        | ID     | 0.9      | A    |
| Pulsed Drain Current<br>(TA = 25 °C, VGS = 10 V) | IDM    | 3.6      | A    |
| Thermal Resistance- Junction to Ambient          | RθJA   | 250      | °C/W |
| Storage Temperature                              | Tstg   | -55~+150 | °C   |
| Junction Temperature                             | TJ     | 150      | °C   |

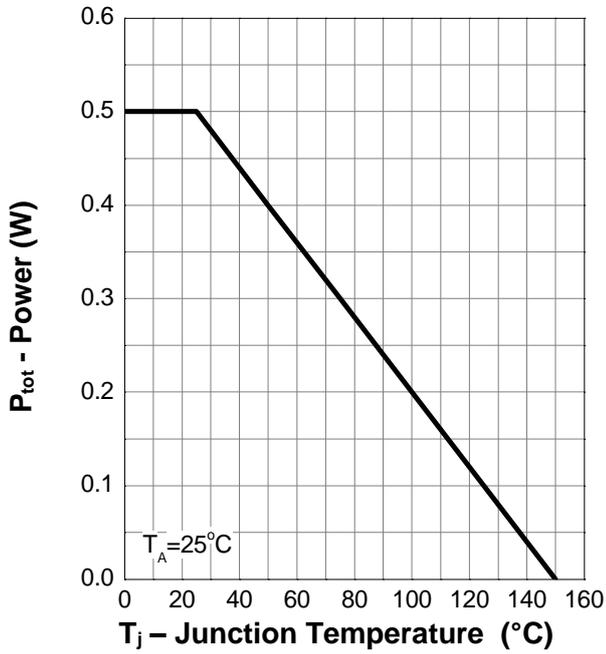
Note : 1.Pulse width ≤ 300μs, duty cycle ≤ 2%

**5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)**

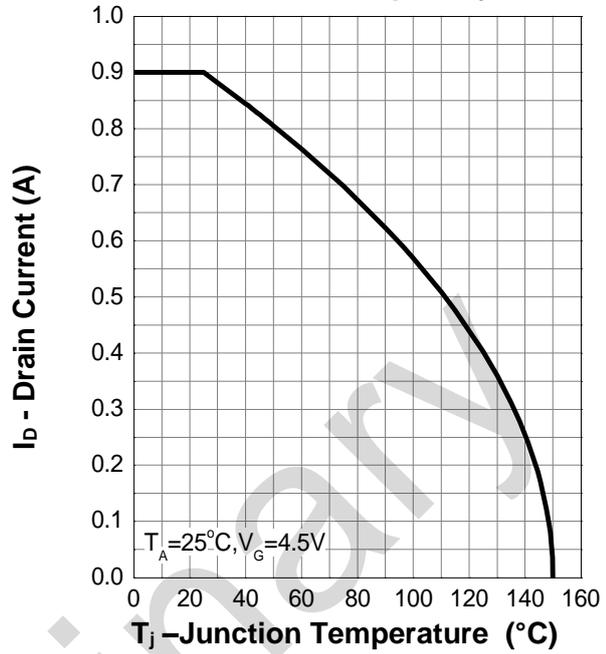
| Characteristic  | Symbol  | Min.    | Typ.                | Max.               | Unit |
|---|---|---------|---------------------|--------------------|------|
| <b>Static Characteristics</b>   |   |         |                     |                    |      |
| Drain-Source Breakdown Voltage<br>(VGS = 0 V, IDS = 250 μA)   | BVDSS   | 20      | -                   | -                  | V    |
| Gate Threshold Voltage<br>(VDS = VGS, IDS = 250 μA)   | VGS(th)   | 0.3     | 0.65                | 1                  | V    |
| Drain Leakage Current<br>(VDS = 16 V, VGS = 0V)<br>(VDS = 16 V, VGS = 0V, TJ = 85 °C)                         | IDSS  | -       | -                   | 1<br>30            | μA   |
| Gate Leakage Current<br>(VGS = ±8 V, VDS = 0 V)   | IGSS  | -       | -                   | ±10                | μA   |
| On-State Resistance<br>(VGS = 4.5 V, IDS = 0.5 A)<br>(VGS = 2.5 V, IDS = 0.2 A)<br>(VGS = 1.8 V, IDS = 0.1 A) | RDS(ON)   | -       | 0.25<br>0.35<br>0.4 | 0.4<br>0.65<br>0.8 | Ω    |
| <b>Diode Characteristics</b>  |   |         |                     |                    |      |
| Diode Forward Voltage<br>(ISD = 0.5 A, VGS = 0 V )  | VSD   | -       | 0.7                 | 1.3                | V    |
| <b>Dynamic</b>  |   |         |                     |                    |      |
| Input Capacitance   | (VGS = 0 V, VDS = 10 V, f=1MHz)                             | Ciss    | -                   | 60.7               | -    |
| Output Capacitance  |   | Coss    | -                   | 9.8                | -    |
| Reverse Transfer Capacitance  |   | Crss    | -                   | 7.6                | -    |
| Turn-On Delay Time  | (VDS = 10 V, VGEN= 4.5 V, RG = 10 Ω, RL = 50 Ω, ID = 0.2 A) | td(on)  | -                   | 6.8                | -    |
| Rise Time   |   | tr      | -                   | 5                  | -    |
| Turn-Off Delay Time   |   | td(off) | -                   | 48                 | -    |
| Fall Time   |   | tf      | -                   | 17                 | -    |
| Total Gate Charge   | (VGS = 4.5 V, VDS = 10 V, IDS = 0.5 A)                      | Qg      | -                   | 0.88               | -    |
| Gate-Source Charge  |   | Qgs     | -                   | 0.13               | -    |
| Gate-Drain Charge   |   | Qgd     | -                   | 0.25               | -    |
| Gate Resistance<br>(VDS=0V, VGS=0V, f=1MHz)   | Rg  | -       | 52                  | -                  | Ω    |

### 6.ELECTRICAL CHARACTERISTICS CURVES

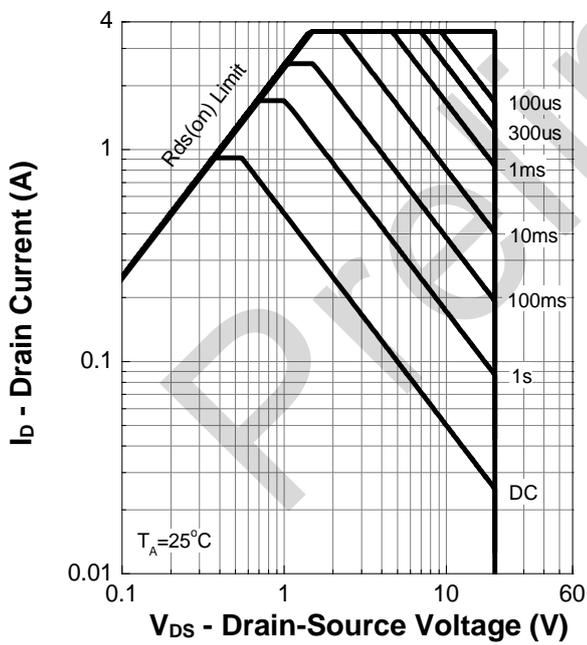
**Power Capability**



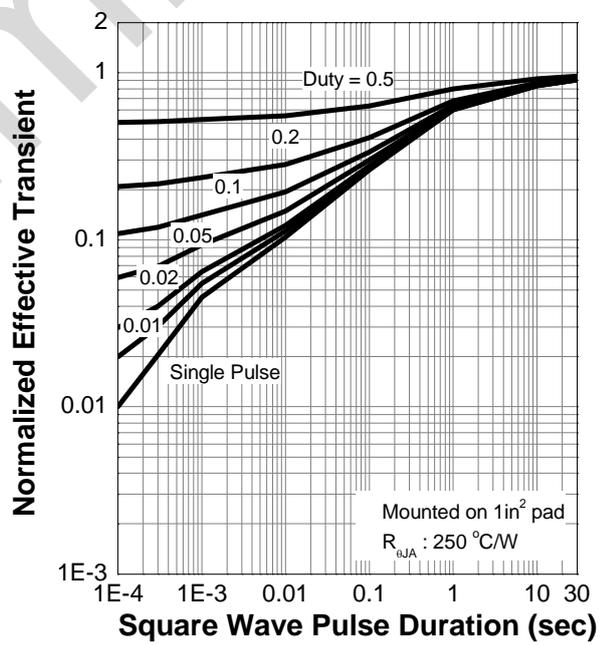
**Current Capability**



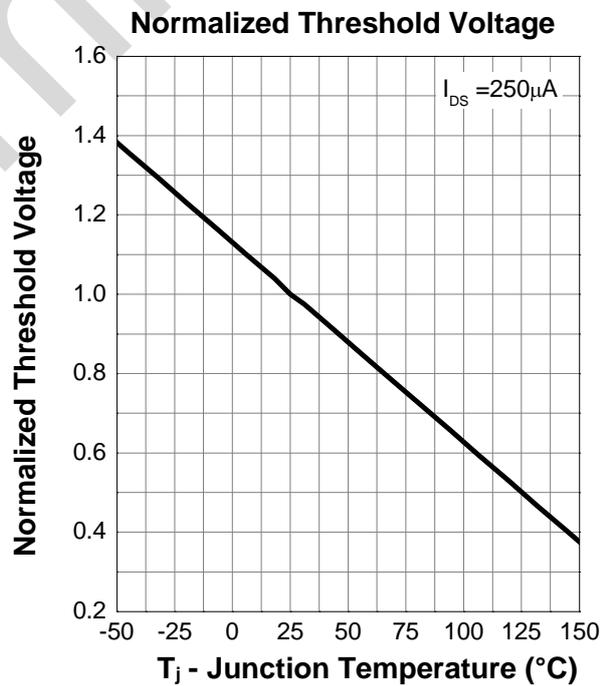
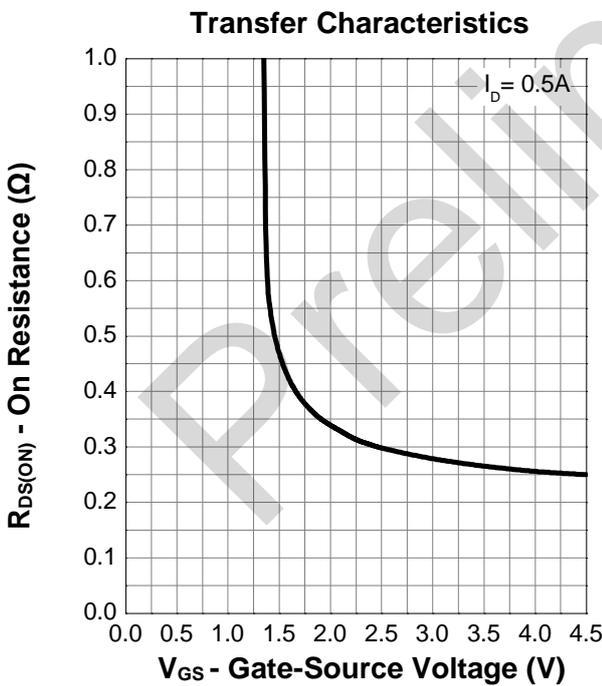
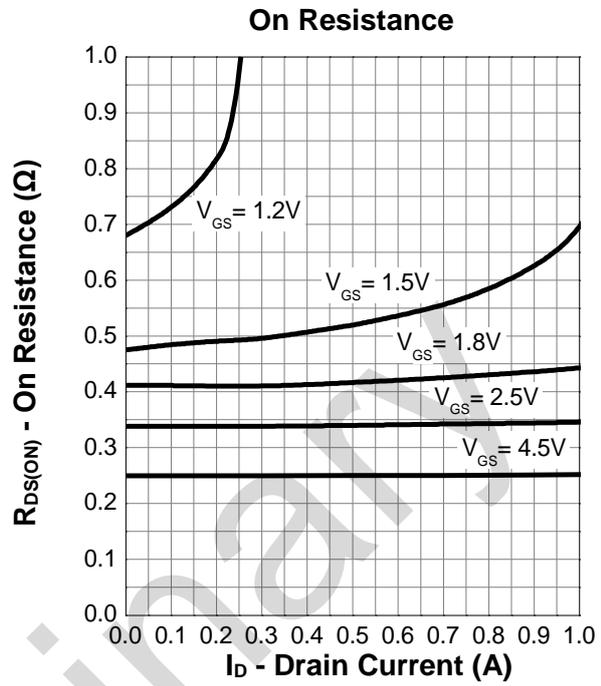
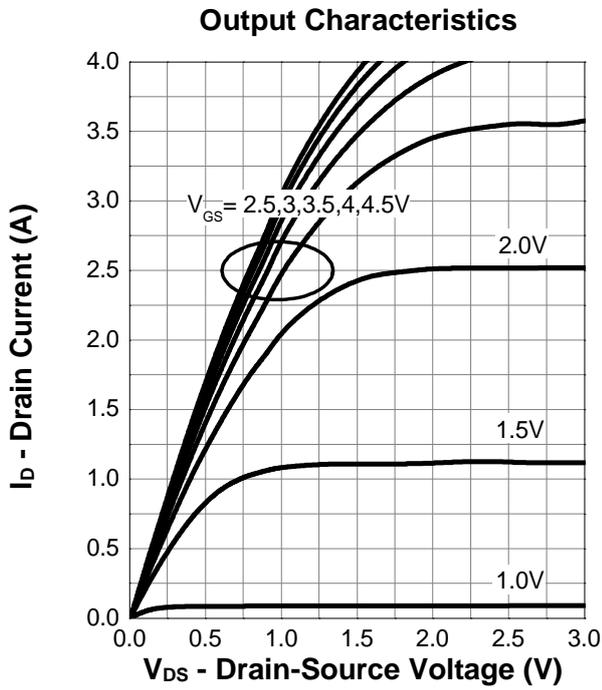
**Safe Operation Area**



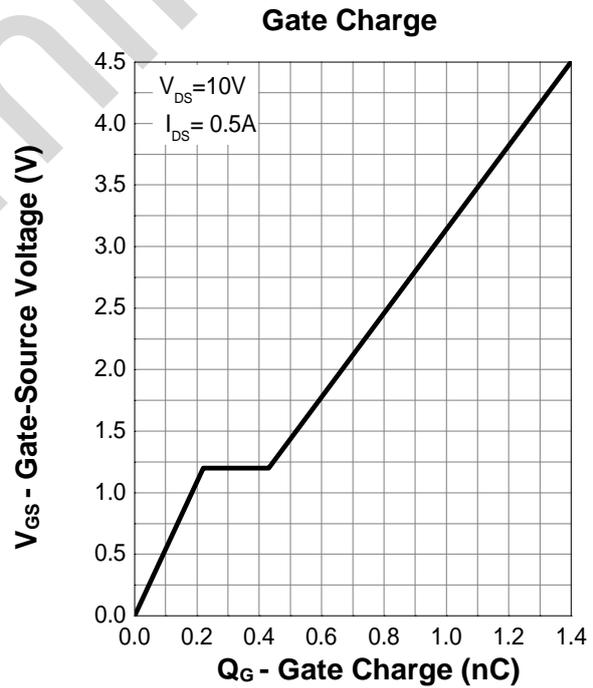
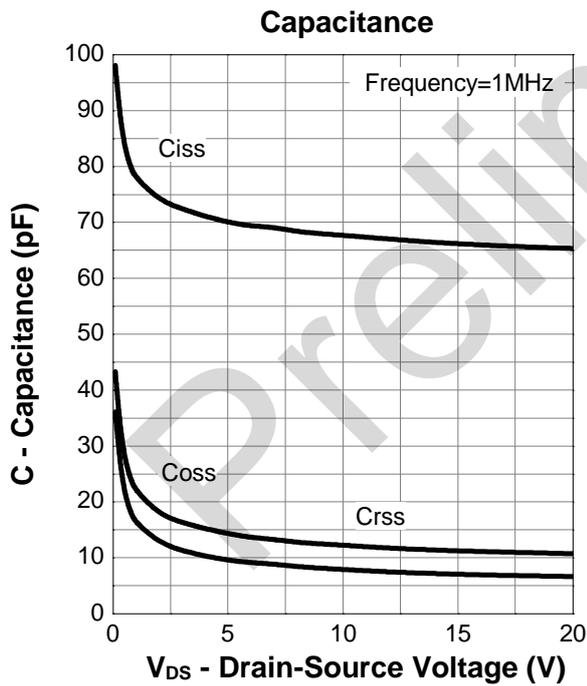
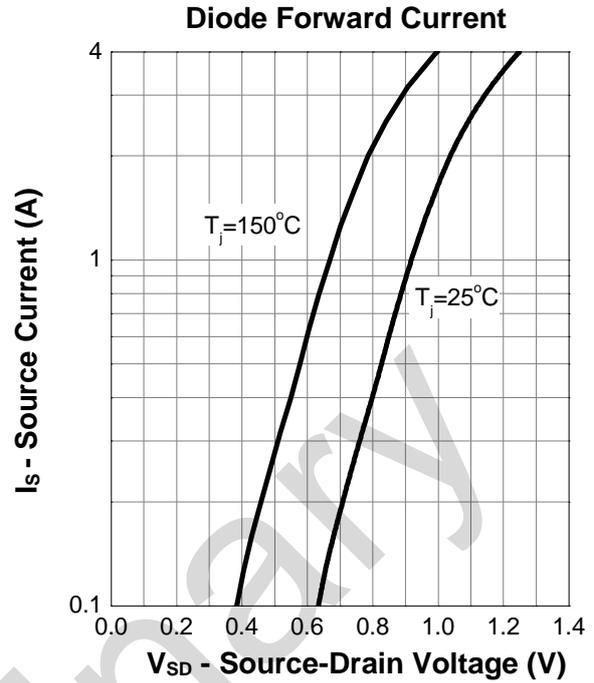
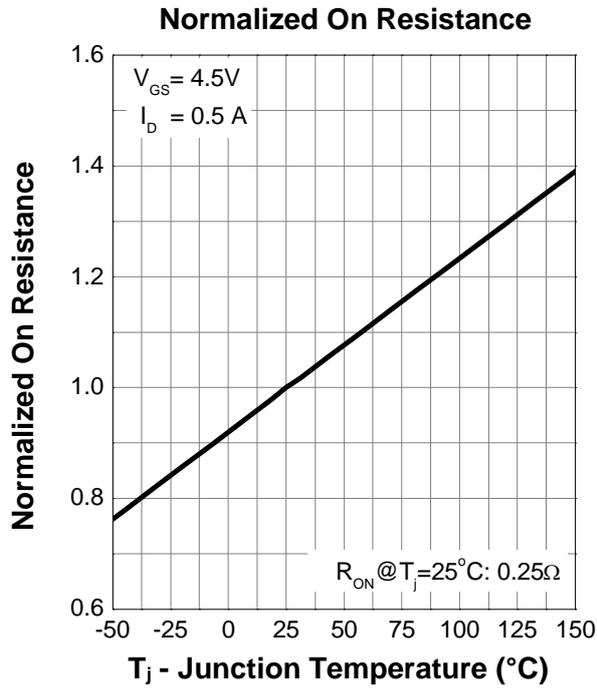
**Transient Thermal Impedance**



6.ELECTRICAL CHARACTERISTICS CURVES(Con.)



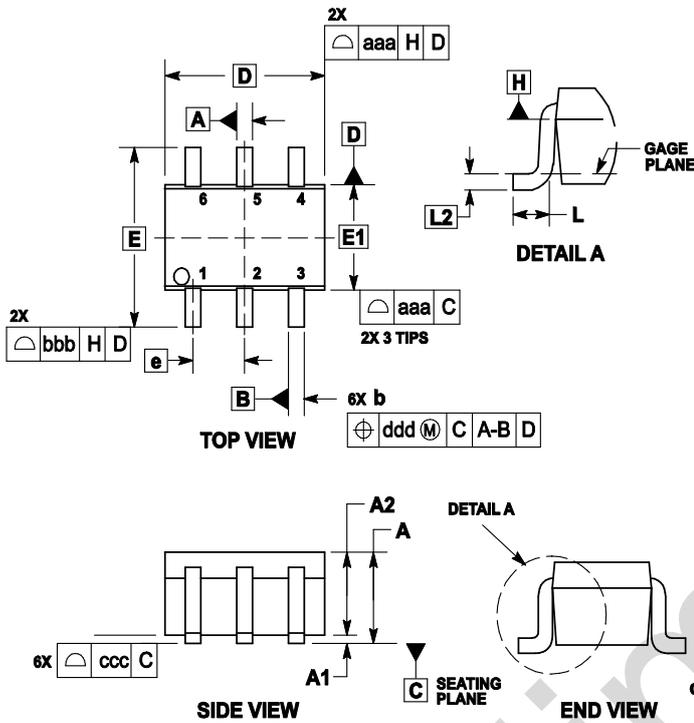
6.ELECTRICAL CHARACTERISTICS CURVES(Con.)



### 7. OUTLINE AND DIMENSIONS

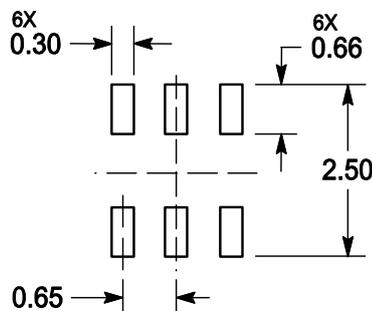
Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



| DIM | MILLIMETERS |      |      | INCHES    |       |       |
|-----|-------------|------|------|-----------|-------|-------|
|     | MIN         | NOM  | MAX  | MIN       | NOM   | MAX   |
| A   | ---         | ---  | 1.10 | ---       | ---   | 0.043 |
| A1  | 0.00        | ---  | 0.10 | 0         | ---   | 0.004 |
| A2  | 0.70        | 0.90 | 1.00 | 0.027     | 0.035 | 0.039 |
| b   | 0.15        | 0.20 | 0.25 | 0.006     | 0.008 | 0.01  |
| C   | 0.08        | 0.15 | 0.22 | 0.003     | 0.006 | 0.009 |
| D   | 1.80        | 2.00 | 2.20 | 0.07      | 0.078 | 0.086 |
| E   | 2.00        | 2.10 | 2.20 | 0.078     | 0.082 | 0.086 |
| E1  | 1.15        | 1.25 | 1.35 | 0.045     | 0.049 | 0.053 |
| e   | 0.65 BSC    |      |      | 0.026 BSC |       |       |
| L   | 0.26        | 0.36 | 0.46 | 0.010     | 0.014 | 0.018 |
| L2  | 0.15 BSC    |      |      | 0.006 BSC |       |       |
| aaa | 0.15        |      |      | 0.01      |       |       |
| bbb | 0.30        |      |      | 0.01      |       |       |
| ccc | 0.10        |      |      | 0.00      |       |       |
| ddd | 0.10        |      |      | 0.00      |       |       |

### 8. SOLDERING FOOTPRINT



## DISCLAIMER

- Curve guarantee in the specification. The curve of test items with electric parameter is used as quality guarantee. The curve of test items without electric parameter is used as reference only.
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[>>LRC\(乐山无线电\)](#)